

1-6-4

## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

<b>Title of Invention</b>	STRUCTURE AND METHOD OF MAKING HETEROJUNCTION BIPOLAR TRANSISTOR HAVING SELF-ALIGNED SILICON-GERMANIUM RAISED EXTRINSIC BASE
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Application Number :

Confirmation Number:

First Named Applicant: Kevin Chan

Attorney Docket Number: FIS920030310US1






Art Unit:

Examiner:

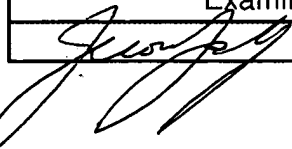
Search string: ( 5128271 or 5494836 or 5506427 or 5962880 or 6346453 ).pn

### US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5128271	1992-07-07	Bronner, et al.			
	2	5494836	1996-02-27	Imai			
	3	5506427	1996-04-09	Imai			
	4	5962880	1999-10-05	Oda, et al.			
	5	6346453	2002-02-12	Kovacic, et al.			

Signature

Examiner Name	Date
	2/05